Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	80	mA
				100	
I_H	I_T =500mA		MAX.	60	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	2000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	25	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	12	μs
t_{off}				80	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =22.5A t_p=380μs	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=150	0.75	V
R_D	Dynamic resistance	T_j=150	27	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=150	1.5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.1	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

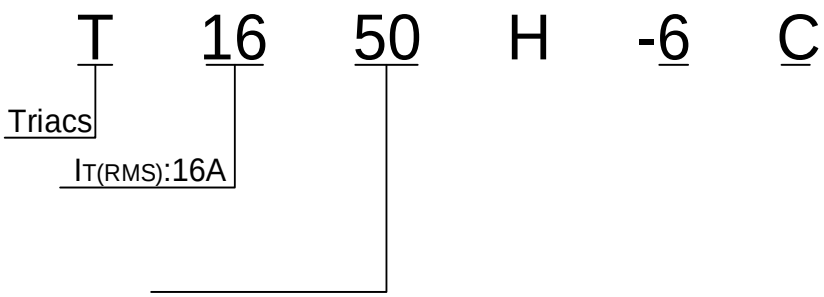

T 16 50 H -6 C
Triacs
IT(RMS):16A

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery



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